

General Description

The 130N85A uses advanced technology and design to provide excellent RDS(ON) .

This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Product Summary

BVDSS	R _{DS(on)} max.	ID
85V	5mΩ	120A

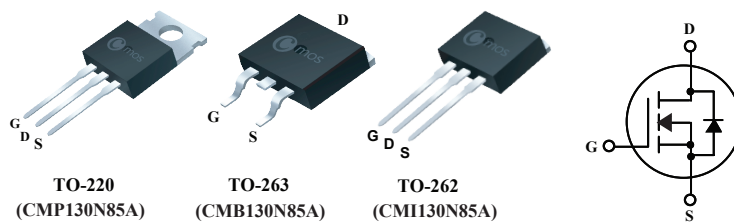
Applications

- Inverters
- Uninterruptible power supply

Features

- Low On-Resistance
- Fast Switching
- RoHS Compliant

TO-220/263/262 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	85	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current	120	A
I _D @T _C =100°C		84	A
I _{DM}	Pulsed Drain Current	480	A
E _{AS}	Drain-Source Avalanche Energy ¹	800	mJ
P _D @T _C =25°C	Total Power Dissipation	170	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient	---	62	°C/W
R _{θJC}	Thermal Resistance Junction-case	---	0.74	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	85	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=50A$	---	4.3	5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=85V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	±100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3.3	---	Ω
Q_g	Total Gate Charge	$I_D=50A$	---	55	---	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=40V$	---	15	---	
Q_{gd}	Gate-Drain Charge	$V_{GS}=10V$	---	13	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=40V$ $R_{G_ext}=3.0\Omega$ $V_{GS}=10V$	---	20	---	ns
T_r	Rise Time		---	39	---	
$T_{d(off)}$	Turn-Off Delay Time		---	45	---	
T_f	Fall Time		---	23	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3900	---	pF
C_{oss}	Output Capacitance		---	1620	---	
C_{rss}	Reverse Transfer Capacitance		---	140	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	120	A
I_{SM}	Pulsed Source Current		---	---	480	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=40A$	---	0.87	1.4	V

Note :

1.The EAS data shows Max. rating . The test condition is $V_{DD}=50V$, $V_{GS}=10V$, $L=1\text{mH}$, $I_{AS}=40A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics

